

NPN Silicon RF power transistor

MRF315

Description:

MRF315 is designed for class C VHF mobile radio power amplifier applications operating.

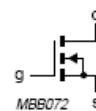
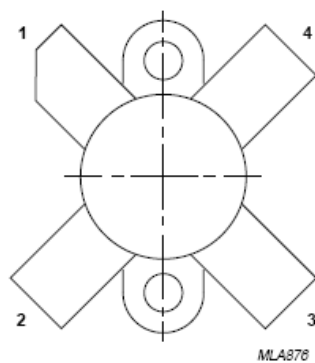
Maximum Ratings at TU = 25

Symbol	Test Conditions	Characteristics		Units
BVCEs	IC=10 mA	Max.	65	V
BVCEO	IC=30 mA	Max.	35	V
BVEBO	IE=5 mA	Max.	4	V
IC		Max.	4	A
Ptot		Max.	110	W
TSTG		Min.	-65	
		Max.	150	
TjM		Max.	200	

Characteristics at TU = 25 (VCC =28 V f=150 MHz)

Symbol	Test Conditions	Characteristics		Units
Pout		Typ.	45	W
GP		Typ.	10	dB
		Typ.	50	%
hFE	IC = 2.9A VCE =10V	Typ.	45	
VCEsat	IC =4A IB =0.8A	Max.	1.2	V
ICES	VCE =35V	Max.	5	mA
CCBO	VCB =28V	Typ.	60	pF
d3		Max.		dB

Drawings:



SOT121